

IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-8 (cancelled)

9. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, ~~characterized in comprising the steps of that~~ maintaining a heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment ~~is at less than 500°C or less, and maintaining a temperature~~ ramping rate in a temperature range from the heat treatment temperature at initial entry to an ~~ultimate a maximum~~ temperature ~~set in a range of 700°C - 900°C, is set to said ramping rate being~~ 1°C/min or less.

10. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, ~~characterized in comprising the steps of that~~ maintaining a heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment ~~is at less than 500°C or less, and maintaining a temperature~~ ramping rate in a temperature range from the heat treatment temperature at initial entry to an ~~ultimate a maximum~~ temperature ~~set in a range of 700°C - 900°C, said ramping rate being is set~~ to 1°C/min or less, so as to make uniform the distribution of an oxide precipitate density of the silicon single crystal wafer after heat treatment.

11. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, ~~comprising the steps of characterized in that~~ controlling heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment and controlling a temperature ramping rate from the heat treatment

Serial No. 09/856,212

temperature at initial entry to ~~an ultimate~~ a maximum temperature ~~set maintaining~~ in a range of 700°C - 900°C ~~are adjusted~~ so as to adjust the distribution of an oxide precipitate density of the silicon single crystal wafer after heat treatment.

12. (original) The method according to Claim 9, ~~characterized in that~~ wherein the oxygen concentration of the perfect crystal is 13×10^{17} atoms/cm³ or less.

13. (currently amended) A silicon single crystal wafer produced by the method according to Claim 12.

Claims 14-23 (cancelled)